

Miniature-package Crystal Oscillator Module ICs

OVERVIEW

The SM5024 series are fundamental crystal oscillator module ICs. They feature an oscillator circuit with built-in capacitors with excellent frequency response and an output buffer with high output drive capability. They are available in miniature 6-pin packages, making them ideal as DIP-type crystal oscillators.

FEATURES

- Operating supply voltage range
 - 3V operation: 2.7 to 3.6V
 - 5V operation: 4.5 to 5.5V
- Up to 30MHz operating frequency range (fundamental oscillation)
- -40 to 85°C operating temperature range
- Oscillator capacitors C_G, C_D built-in
- lacktriangle Feedback resistor R_f built-in
- f_O, f_O/2, f_O/4, f_O/8 output frequency, determined by internal connection
- Output drive capability
 - $8mA (V_{DD} = 2.7V)$
 - $16\text{mA} (V_{DD} = 4.5\text{V})$
- Output three-state function built-in High impedance outputs in standby mode
- CMOS output duty level (1/2VDD)
- Molybdenum-gate CMOS process
- Package: SOT23-6 (SM5024×××H)

APPLICATIONS

■ DIP-type crystal oscillator modules

SERIES CONFIGURATION

Version	Operating	Recommended operating		[pF] Output Output INHN input		[pF] Output Output INHN input						y mode
version	Supply voltage range [V]	frequency range ¹ [MHz]	C _G	C _D	duty level	· · ·				Output state		
SM5024AL1H						f _O						
SM5024AL2H	2.7 to 5.5	4 to 30	8	10	CMOS	f _O /2	TTL	V				
SM5024AL3H	2.7 10 5.5	4 10 30	0	10	CIVIOS	f _O /4	111	Yes	Hi-Z			
SM5024AL4H						f _O /8						

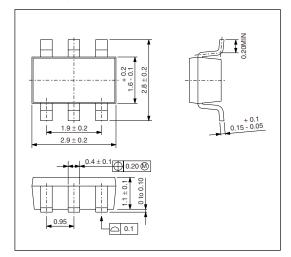
The recommended operating frequency is a yardstick value derived from the crystal used for NPC characteristics authentication. However, the oscillator frequency band is not guaranteed. Specifically, the characteristics can vary greatly due to crystal characteristics and mounting conditions, so the oscillation characteristics of components must be carefully evaluated.

ORDERING INFORMATION

Device	Package
SM5024×××H	SOT23-6

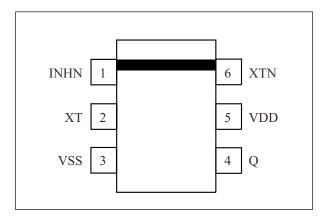
PACKAGE DIMENSIONS

(Unit: mm)



PINOUT

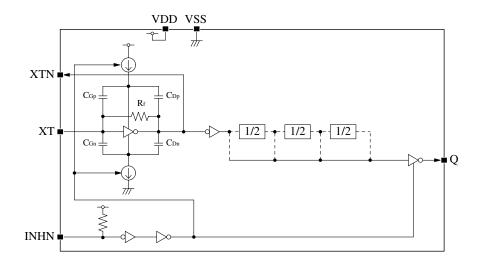
(Top view)



PIN DESCRIPTION

Name	I/O		Description				
INHN	I	Output state control input. H Pull-up resistor built-in.	ligh impedance when LOW.				
XT	1	Amplifier input	Crystal connection pins.				
XTN	0	Amplifier output	Crystal is connected between XT and XTN.				
VSS	-	Ground					
Q	0	Output. Output frequency (f	o, f _O /2, f _O /4, f _O /8) determined by internal connection				
VDD	-	Supply voltage					

BLOCK DIAGRAM



INHN = LOW active

Notes. The SM5024 series reduce crystal current by limiting driving current of oscillating-stage inverter and inhibiting oscillating amplitude. Depending on the characteristics of using crystal or the mounting condition, they may not oscillate normally. Please evaluate the oscillation start-up characteristics adequately with your actual device. When this device is used for buffer application, please pay attention to input amplitude to the XT pin. If it's low input amplitude, the SM5024 series may not operate normally.

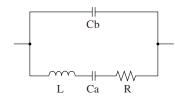
FUNCTIONAL DESCRIPTION

Standby Function

When INHN goes LOW, the oscillator stops and the oscillator output on Q becomes high impedance.

INHN	Q	Oscillator
HIGH (or open)	Any f _O , f _O /2, f _O /4, or f _O /8 output frequency	Normal operation
LOW	High impedance	Stopped

Current consumption and Output waveform with NPC's standard crystal



f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
30	5.26	2.82	1.00	2.68

SPECIFICATIONS

Absolute Maximum Ratings

 $V_{SS} = 0V$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V _{DD}		-0.5 to +7.0	V
Input voltage range	V _{IN}		-0.5 to V _{DD} + 0.5	V
Output voltage range	V _{OUT}		-0.5 to V _{DD} + 0.5	V
Operating temperature range	T _{opr}		-40 to +85	°C
Storage temperature range	T _{STG}		-55 to +125	°C
Output current	l _{out}		20	mA
Power dissipation	P _D		250	mW

Recommended Operating Conditions

3V operation

 $V_{SS} = 0V$, $f \le 30MHz$, $C_L \le 15pF$ unless otherwise noted.

Parameter	Symbol	Condition		Rating		Unit
Operating supply voltage	V _{DD}		2.7	-	3.6	V
Input voltage	V _{IN}		V _{SS}	-	V _{DD}	V
Operating temperature	T _{OPR}		-20	-	+80	°C

5V operation

 $V_{SS} = 0V$, $f \le 30MHz$, $C_L \le 50pF$ unless otherwise noted

Parameter	Symbol	Condition	Rating			Unit
Operating supply voltage	V _{DD}		4.5	_	5.5	٧
Input voltage	V _{IN}		V _{SS}	-	V _{DD}	٧
Operating temperature	T _{OPR}		-40	-	+85	°C

Electrical Characteristics

3V operation

 $V_{SS} = 0V$, recommended operating conditions unless otherwise noted.

Parameter	Cumbal	Condition			Rating		Unit	
Parameter	Symbol	Condition		min	typ	max	J.III	
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 2.7V, I _{OH} =	BmA	2.1	2.4	-	٧	
LOW-level output voltage	V _{OL}	Q: Measurement cct 2, V _{DD} = 2.7V, I _{OL} = 8	BmA	_	0.3	0.5	٧	
HIGH-level input voltage	V _{IH}	INHN		2.0	-	-	٧	
LOW-level input voltage	V _{IL}	INHN		-	-	0.5	٧	
Outrot leake as a surrent		Q: Measurement cct 2, INHN = LOW, V _{DD} = 3.6V	$V_{OH} = V_{DD}$	-	-	10	μA	
Output leakage current	Iz		V _{OL} = V _{SS}	-	-	10	μΑ	
			SM5024AL1H	-	4	8	mA	
Command as a summation		Measurement cct 3, load cct 1,	SM5024AL2H	-	2.5	5	mA	
Current consumption	I _{DD1}	INHN = open, C _L = 15pF, f = 30MHz	SM5024AL1H – 3, load cct 1, SM5024AL2H –	2	4	mA		
			SM5024AL4H	-	1.5	- 0.5 - 0.5 10 10 8 5	mA	
INHN pull-up resistance	R _{UP}	Measurement cct 4	'	25	100	250	kΩ	
Feedback resistance	R _f	Measurement cct 5		200	600	1000	kΩ	
Duilt in consitones	C _G			7.44	8	8.56	pF	
Built-in capacitance	C _D	Design value. A monitor pattern on a wafe	i is lesieu.	9.3	10	10.7	pF	

5V operation

 $V_{SS} = 0V$, recommended operating conditions unless otherwise noted.

Parameter	Cumbal	Condition	Condition				Unit
Parameter	Symbol	Condition		min	typ	max - 0.5 - 0.8 10 10 26 14 8 6 250	Unit
HIGH-level output voltage	V _{OH}	Q: Measurement cct 1, V _{DD} = 4.5V, I _{OH} =	16mA	3.9	4.2	-	٧
LOW-level output voltage	V _{OL}	Q: Measurement cct 2, V _{DD} = 4.5V, I _{OL} =	16mA	-	0.3	0.5	٧
HIGH-level input voltage	V _{IH}	INHN		2.0	-	-	٧
LOW-level input voltage	V _{IL}	INHN		-	-	0.8	٧
Output leakage current		Q: Measurement cct 2, INHN = LOW,	$V_{OH} = V_{DD}$	-	-	10	μA
Output leakage current	l I _Z	V ₀	V _{OL} = V _{SS}	-	-	10	μA
		Measurement cct 3, load cct 1,	SM5024AL1H	-	13	26	mA
Current concumption			SM5024AL2H	-	7	14	mA
Current consumption	I _{DD2}	INHN = open, C _L = 50pF, f = 30MHz	SM5024AL3H	-	4	8	mA
			SM5024AL4H	-	3	- 0.5 - 0.8 10 10 26 14 8 6	mA
INHN pull-up resistance	R _{UP}	Measurement cct 4	•	25	100	250	kΩ
Feedback resistance	R _f	Measurement cct 5		200	600	1000	kΩ
Built in canceitance	C _G	Decign value A monitor nottern on a work	ur in tootod	7.44	8	8.56	pF
Built-in capacitance	C _D	Design value. A monitor pattern on a wafe	ย เจ เฮอเฮน.	10 - 10 - 110 - 13 26 - 7 14 - 4 8 - 3 6 25 100 250 200 600 1000 7.44 8 8.56	pF		

Switching Characteristics

3V operation

 $V_{\rm DD}$ = 2.7 to 3.6V, $V_{\rm SS}$ = 0V, Ta = -20 to +80°C unless otherwise noted.

Parameter	Symbol	mbol Condition		Rating			
Parameter	Syllibol	Condition	min	typ	max	Unit	
Output rise time	t _{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$, C_L = 15pF	-	5	10	ns	
Output fall time	t _{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$, C_L = 15pF	-	5	10	ns	
Output duty cycle ¹	Duty1	Measurement cct 6, load cct 1, V_{DD} = 3.0V, Ta = 25°C, C_L = 15pF, f \leq 30MHz	45	-	55	%	
Output disable delay time ²	t _{PLZ}	Measurement cct 6, load cct 1, V _{DD} = 3.0V, Ta = 25°C,	-	-	100	ns	
Output enable delay time ²	t _{PZL}	$C_L = 15pF$	-	-	100	ns	

^{1.} The duty cycle characteristic is checked the sample chips of each production lot.

5V operation

 $V_{\rm DD}$ = 4.5 to 5.5V, $V_{\rm SS}$ = 0V, Ta = -40 to +85°C unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
Faiailletei	Syllibol	Condition		min	typ	max	Ollit
Output rise time	t _{r1}	Measurement cct 6, load cct 1,	C _L = 15pF	-	2.5	5	ns
Output rise time	t _{r2}	0.1V _{DD} to 0.9V _{DD}	-	5	10	113	
Output fall time	t _{f1}	Measurement cct 6, load cct 1,	C _L = 15pF	-	2.5	5	ns
Output fail time	t _{f2}	0.9V _{DD} to 0.1V _{DD}	C _L = 50pF	-	5	10	115
Output duty cycle ¹	Duty2	$\label{eq:measurement} \begin{split} &\text{Measurement cct 6, load cct 1, V}_{DD} = 5.0\text{V,} \\ &C_L = 50\text{pF, f} \leq 30\text{MHz} \end{split}$	easurement cct 6, load cct 1, V _{DD} = 5.0V, Ta = 25°C,		-	55	%
Output disable delay time ²	t _{PLZ}	Measurement cct 6, load cct 1, V _{DD} = 5.0V, Ta = 25°C,		-	-	100	ns
Output enable delay time ²	t _{PZL}	C _L = 15pF		_	-	100	ns

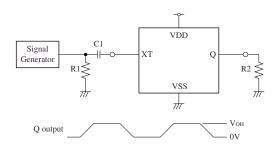
 $^{1. \ \ \, \}text{The duty cycle characteristic is checked the sample chips of each production lot.}$

^{2.} Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

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MEASUREMENT CIRCUITS

Measurement cct 1

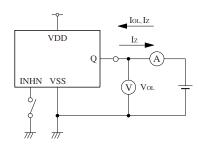


2.0Vp-p, 10MHz sine wave input signal (3V operation) 3.5Vp-p, 10MHz sine wave input signal (5V operation)

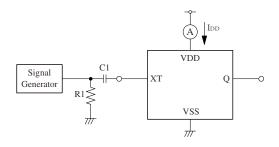
C1: 0.001μF R1: 50Ω

R2: 263Ω (3V operation) 244Ω (5V operation)

Measurement cct 2

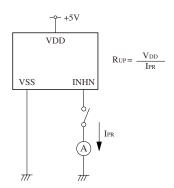


Measurement cct 3

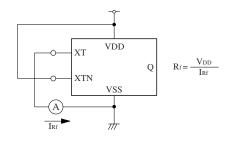


2.0Vp-p, 30MHz sine wave input signal (3V operation) 3.5Vp-p, 30MHz sine wave input signal (5V operation) C1: $0.001\mu F$ R1: 50Ω

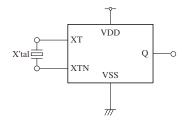
Measurement cct 4



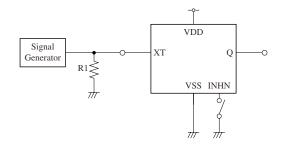
Measurement cct 5



Measurement cct 6

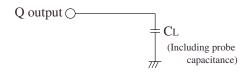


Measurement cct 7



R1: 50Ω

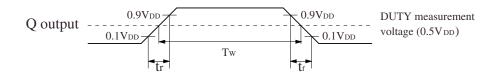
Load cct 1



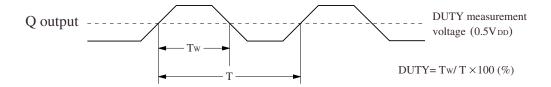
$$\begin{split} &C_L = 15 pF; \, t_{r1}, \, t_{f1}, \, Duty1, \, I_{DD1} \\ &C_L = 50 pF; \, t_{r2}, \, t_{f2}, \, Duty2, \, I_{DD2} \end{split}$$

Switching Time Measurement Waveform

Output duty level, tr, tf

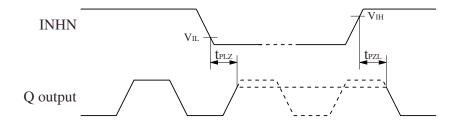


Output duty cycle



Output Enable/Disable Delay

When the device is in standby, the oscillator stops. When standby is released, the oscillator starts and stable oscillator output occurs after a short delay.



INHN input waveform $tr = tf \le 10ns$

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